

950V N-Channel MOSFET

Description

The MS6N95 is a N-channel enhancement-mode MOSFET, providing the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost effectiveness. The TO-220 package is universally preferred for all commercial-industrial applications

Features

- RDS(on) (Max 2.4 Ω)@VGS=10V
- Gate Charge (Typical 33nC)
- · Improved dv/dt Capability, High Ruggedness
- 100% Avalanche Tested
- Maximum Junction Temperature Range (150°C)
- · RoHS compliant package

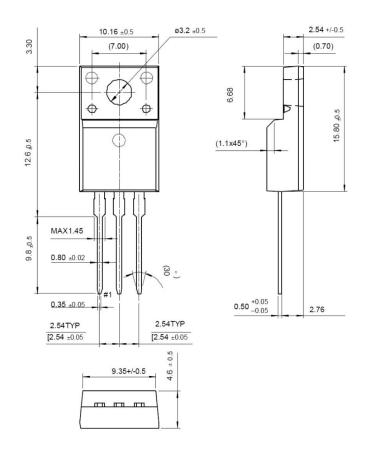
Application

- Adapter
- · Switching Mode Power Supply

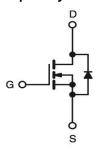
Packing & Order Information

50/Tube; 1,000/Box





Graphic symbol



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings (Tc=25°C unless otherwise specified)						
Symbol	Parameter	Value	Unit			
V_{DSS}	Drain-Source Voltage	950	V			
I _D	Drain Current -Continuous (TC=25°C)	6	А			
	Drain Current -Continuous (TC=100°C)	3.8	А			
I _{DM}	Drain Current –Pulsed	24	А			
V _{GS}	Gate-Source Voltage	±30	V			
E _{AS}	Single Pulsed Avalanche Energy	650	mJ			
E _{AR}	Repetitive Avalanche Energy	16.7	mJ			
dv/dt	Peak Diode Recovery dv/dt	4.5	V/ns			



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Symbol	Parameter	Value	Unit
_	Power Dissipation (TC=25°C)	56	W
P_D	- Derate above 25°C	0.48	W/°C
T _J /T _{STG}	Operating and Storage Temperature Range	-55 to +150	°C
T _L	Maximum lead temperature for soldering purposes, 1/8" from	200	°C
	case for 5 seconds	300	°C

[•]Drain current limited by maximum junction temperature

Thermal Resistance Characteristics					
Symbol	Parameter	Тур.	Max.	Units	
$R_{ heta JC}$	Junction-to-Case		2.25	°C/W	
$R_{\theta JA}$	Junction-to-Ambient		62.5	C/VV	

On Characteristics						
Symbol	Parameter	Test Conditions	Min	Тур.	Max.	Units
V_{GS}	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	3.0		5.0	V
R _{DS(ON)}	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, I_{D} = 3 \text{ A}$		1.95	2.40	Ω

Off Chara	Off Characteristics					
Symbol	Parameter	Test Conditions	Min	Тур.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V} , I_D = 250 \mu A$	900			V
ΔBV_{DSS} $/\Delta T_{J}$	Breakdown Voltage Temperature Coefficient	I _D =250μA , Referenced to 25°C		0.6		V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 950 V , V _{GS} = 0 V V _{DS} = 720 V , V _C = 125 °C			10 100	μA
I _{GSSF}	Gate-Body Leakage Current,Forward	$V_{GS} = 30 \text{ V}$, $V_{DS} = 0 \text{ V}$			100	μA
I _{GSSR}	Gate-Body Leakage Current,Reverse	$V_{GS} = -30V , V_{DS} = 0 V$			-100	nA

Dynamic Characteristics							
Symbol	Parameter	Test Conditions	Min	Тур.	Max.	Units	
C _{ISS}	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ $f = 1.0 \text{MHz}$		1500		pF	
C _{oss}	Coss Output Capacitance			120		pF	
C _{RSS}	Crss Reverse Transfer Capacitance	1 = 1.001112		12		pF	



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Switching	Switching Characteristics							
Symbol	Parameter	Test Conditions	Min	Тур.	Max.	Units		
t _{d(on)}	Turn-On Time			50		ns		
t _r	Turn-On Rise Time	$V_{DS} = 450 \text{ V}, I_D = 6 \text{ A},$		100		ns		
t _{d(off)}	Turn-Off Delay Time	$R_G = 25 \Omega$		50		ns		
tf	Turn-Off Fall Time			60		ns		
Q_g	Total Gate Charge			33		nC		
Q_{gs}	Gate-Source Charge	$V_{DS} = 720 \text{ V}, I_{D} = 6 \text{ A},$ $V_{GS} = 10 \text{ V}$		10		nC		
Q_{gd}	Gate-Drain Charge	V GS - 10 V		13		nC		

Symbol	Parameter	Test Conditions	Min	Тур.	Max.	Units
I _S	Continuous Source-Drain Diode Forward Current				6.0	
I _{SM}	ISM Pulsed Source-Drain Diode Forward Current				24.0	Α
V _{SD}	Source-Drain Diode Forward Voltage	I _S = 6 A , V _{GS} = 0 V			1.4	V
T _{rr}	Reverse Recovery Time	I _S = 6 A , V _{GS} = 0 V		0.65		ns
Q _{rr}	Reverse Recovery Charge	diF/dt=100A/µs		7.0		μC

Notes:

- 1. Repeativity rating: pulse width limited by junction temperature
- 2. L = 34.0mH, I_{AS} =6.0A, V_{DD} = 50V, R_{G} = 25 $\!\Omega$, Starting TJ = 25 $\!^{\circ}C$
- 3. $I_{SD} \le 6.0A$, di/dt $\le 200A/us$, VDD $\le BVDSS$, Starting TJ = 25°C
- 4. Pulse Test : Pulse Width ≤ 300us, Duty Cycle ≤ 2%
- 5. Essentially independent of operating temperature.



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